

STARPOWER

SEMICONDUCTOR

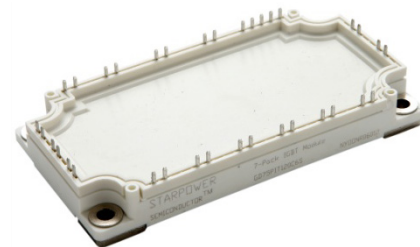
IGBT

GD50PIL120C6S

1200V/50A PIM in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.



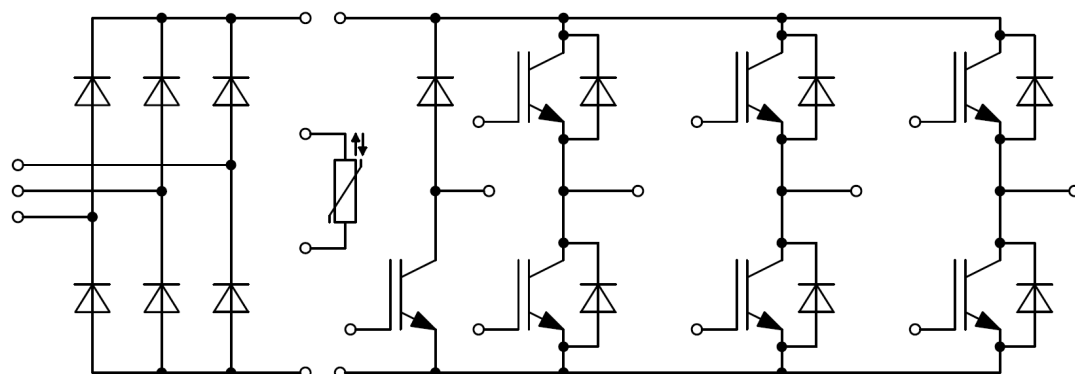
Features

- Low $V_{CE(sat)}$ SPT+ IGBT technology
- 10 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT-inverter**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	100	A
	@ $T_C=100^{\circ}\text{C}$	50	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	100	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	444	W

Diode-inverter

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	50	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	100	A

Diode-rectifier

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1600	V
I_O	Average Output Current 50Hz/60Hz,sine wave	50	A
I_{FSM}	Surge Forward Current $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	850	A
I^2t	I^2t -value, $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	3610	A^2s

IGBT-brake

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 30	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$	86	A
	@ $T_C=100^{\circ}\text{C}$	50	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	100	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	297	W

Diode-brake

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	25	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	50	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature(inverter,brake)	175	$^{\circ}\text{C}$
	Maximum Junction Temperature (rectifier)	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}, t=1\text{min}$	2500	V

IGBT-inverter Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=50\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.85	2.30	V
		$I_C=50\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		2.05		
		$I_C=50\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		2.10		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.0	5.9	7.0	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			10		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		4.29		nF
C_{res}	Reverse Transfer Capacitance			0.20		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.54		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=50\text{A}, R_G=15\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		392		ns
t_r	Rise Time			74		ns
$t_{d(off)}$	Turn-Off Delay Time			379		ns
t_f	Fall Time			380		ns
E_{on}	Turn-On Switching Loss			6.29		mJ
E_{off}	Turn-Off Switching Loss			3.22		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=50\text{A}, R_G=15\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		403		ns
t_r	Rise Time			75		ns
$t_{d(off)}$	Turn-Off Delay Time			408		ns
t_f	Fall Time			381		ns
E_{on}	Turn-On Switching Loss			7.30		mJ
E_{off}	Turn-Off Switching Loss			5.22		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=50\text{A}, R_G=15\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		410		ns
t_r	Rise Time			76		ns
$t_{d(off)}$	Turn-Off Delay Time			420		ns
t_f	Fall Time			382		ns
E_{on}	Turn-On Switching Loss			7.75		mJ
E_{off}	Turn-Off Switching Loss			5.70		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		270		A

Diode-inverter Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=50\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.80	2.25	V
		$I_F=50\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		1.85		
		$I_F=50\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		1.85		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=50\text{A},$ $-di/dt=830\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		3.3		μC
I_{RM}	Peak Reverse Recovery Current			34		A
E_{rec}	Reverse Recovery Energy			1.28		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=50\text{A},$ $-di/dt=830\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		6.5		μC
I_{RM}	Peak Reverse Recovery Current			47		A
E_{rec}	Reverse Recovery Energy			2.03		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=50\text{A},$ $-di/dt=830\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		7.2		μC
I_{RM}	Peak Reverse Recovery Current			50		A
E_{rec}	Reverse Recovery Energy			2.25		mJ

Diode-rectifier Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=50\text{A}, T_j=150^{\circ}\text{C}$		1.03		V
I_R	Reverse Current	$T_j=150^{\circ}\text{C}, V_R=1600\text{V}$			1.5	mA

IGBT-brake Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=50\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.70	2.15	V
		$I_C=50\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		1.95		
		$I_C=50\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		2.00		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.0	5.7	6.5	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			100	nA
R_{Gint}	Internal Gate Resistance			/		Ω
C_{ies}	Input Capacitance	$V_{CE}=30\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		3.70		nF
C_{res}	Reverse Transfer Capacitance			0.12		nF
Q_G	Gate Charge	$V_{GE}=15\text{V}$		0.25		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=50\text{A}, R_G=15\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		209		ns
t_r	Rise Time			46		ns
$t_{d(off)}$	Turn-Off Delay Time			266		ns
t_f	Fall Time			285		ns
E_{on}	Turn-On Switching Loss			3.44		mJ
E_{off}	Turn-Off Switching Loss			2.88		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=50\text{A}, R_G=15\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		205		ns
t_r	Rise Time			52		ns
$t_{d(off)}$	Turn-Off Delay Time			284		ns
t_f	Fall Time			395		ns
E_{on}	Turn-On Switching Loss			4.61		mJ
E_{off}	Turn-Off Switching Loss			4.54		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=50\text{A}, R_G=15\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		205		ns
t_r	Rise Time			54		ns
$t_{d(off)}$	Turn-Off Delay Time			295		ns
t_f	Fall Time			403		ns
E_{on}	Turn-On Switching Loss			5.06		mJ
E_{off}	Turn-Off Switching Loss			4.99		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		200		A

Diode-brake Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=25\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		2.10	2.55	V
		$I_F=25\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		2.15		
		$I_F=25\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		2.15		
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=25\text{A},$ $-di/dt=575\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		1.3		μC
I_{RM}	Peak Reverse Recovery Current			22		A
E_{rec}	Reverse Recovery Energy			0.42		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=25\text{A},$ $-di/dt=575\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		3.4		μC
I_{RM}	Peak Reverse Recovery Current			23		A
E_{rec}	Reverse Recovery Energy			1.04		mJ
Q_r	Recovered Charge	$V_R=600\text{V}, I_F=25\text{A},$ $-di/dt=575\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		3.8		μC
I_{RM}	Peak Reverse Recovery Current			26		A
E_{rec}	Reverse Recovery Energy			1.20		mJ

NTC Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{25}	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of R_{100}	$T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$	-5		5	%
P_{25}	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance		60		nH
$R_{CC'+EE'}$ $R_{AA'+CC'}$	Module Lead Resistance, Terminal to Chip		4.00 2.00		m Ω
R_{thJC}	Junction-to-Case (per IGBT-inverter) Junction-to-Case (per Diode-inverter) Junction-to-Case (per Diode-rectifier) Junction-to-Case (per IGBT-brake) Junction-to-Case (per Diode-brake)			0.338 0.619 0.635 0.504 1.266	K/W
R_{thCH}	Case-to-Heatsink (per IGBT-inverter) Case-to-Heatsink (per Diode-inverter) Case-to-Heatsink (per Diode-rectifier) Case-to-Heatsink (per IGBT-brake) Case-to-Heatsink (per Diode-brake) Case-to-Heatsink (per Module)		0.121 0.221 0.227 0.180 0.452 0.009		K/W
M	Mounting Torque, Screw:M5	3.0		6.0	N.m
G	Weight of Module		300		g

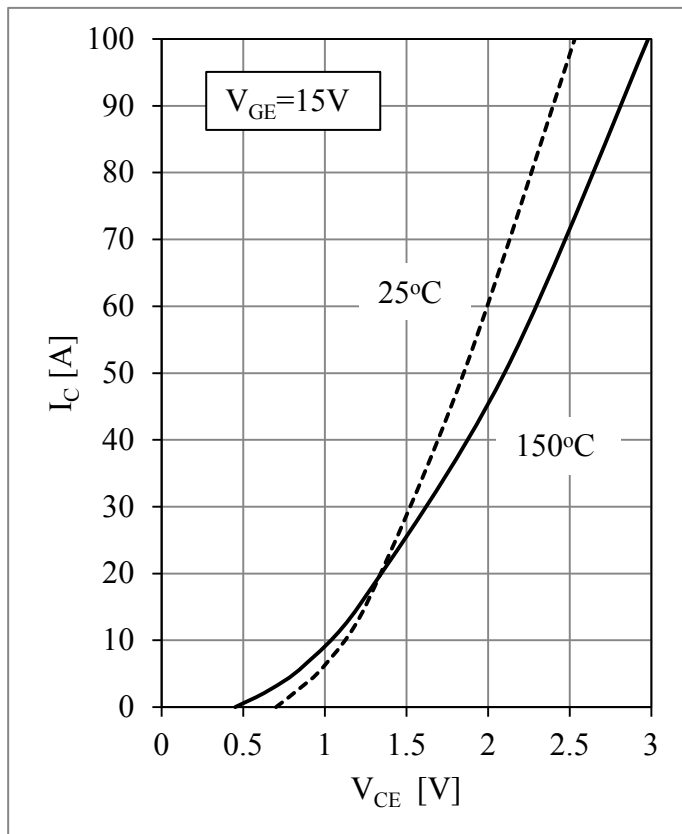


Fig 1. IGBT-inverter Output Characteristics

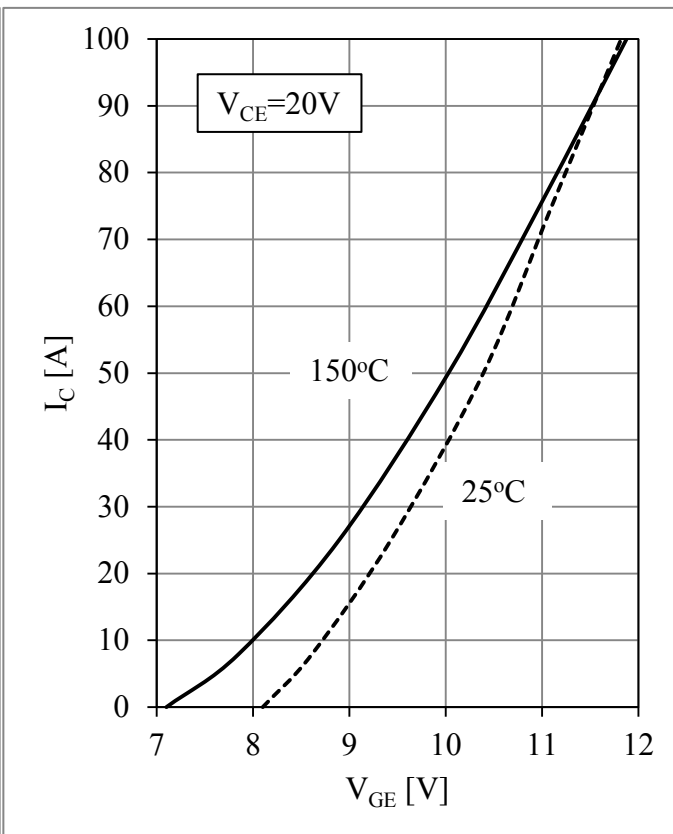
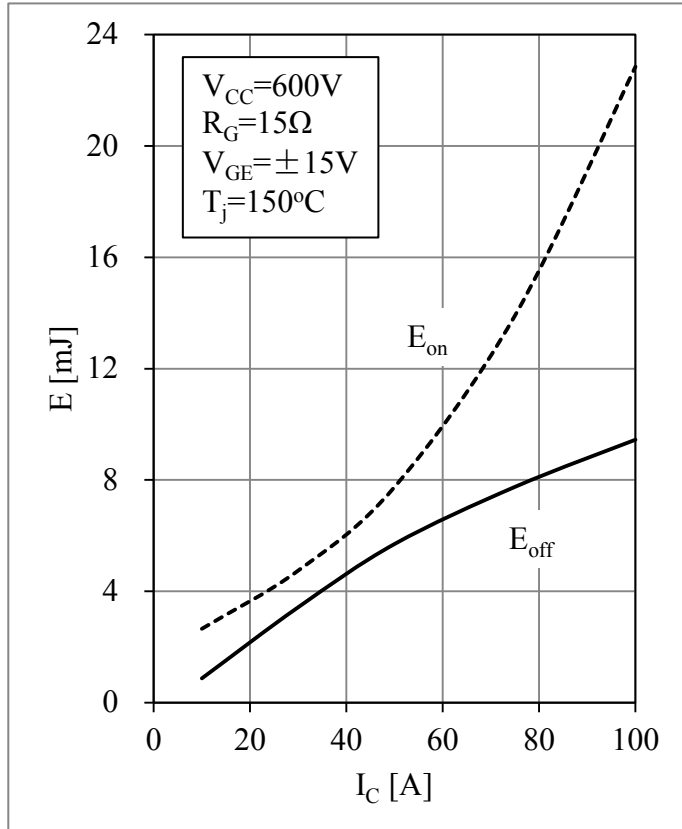
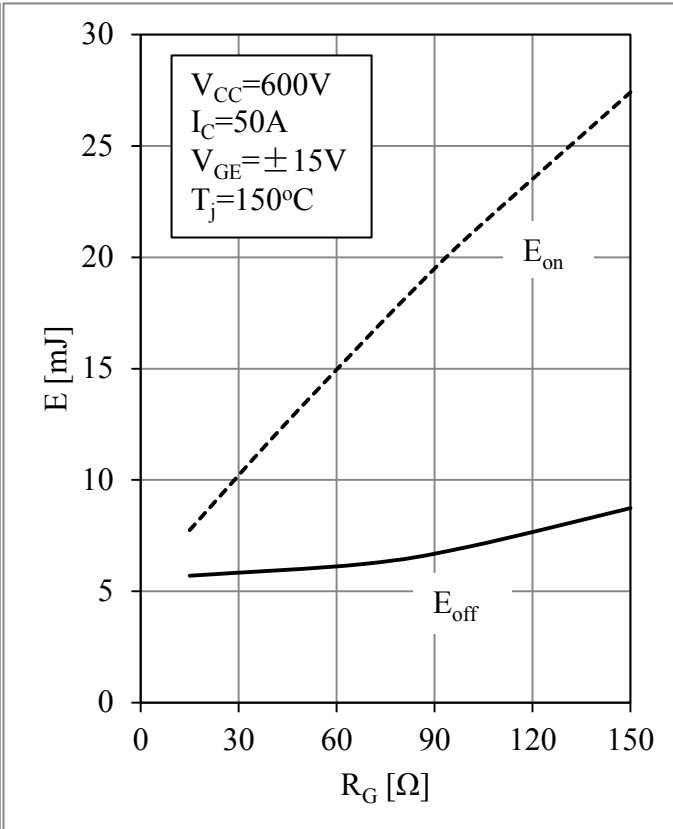


Fig 2. IGBT-inverter Transfer Characteristics

Fig 3. IGBT-inverter Switching Loss vs. I_C Fig 4. IGBT-inverter Switching Loss vs. R_G

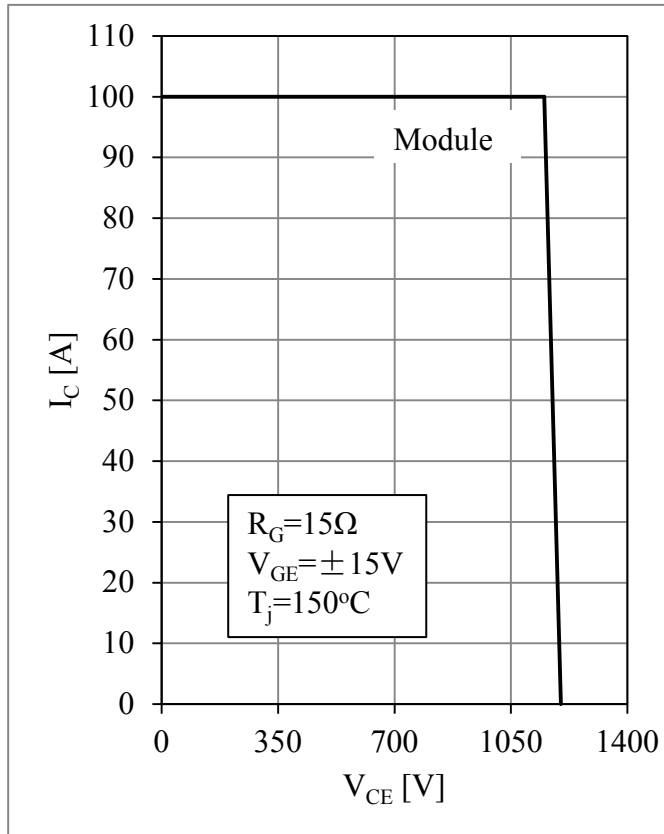


Fig 5. IGBT-inverter RBSOA

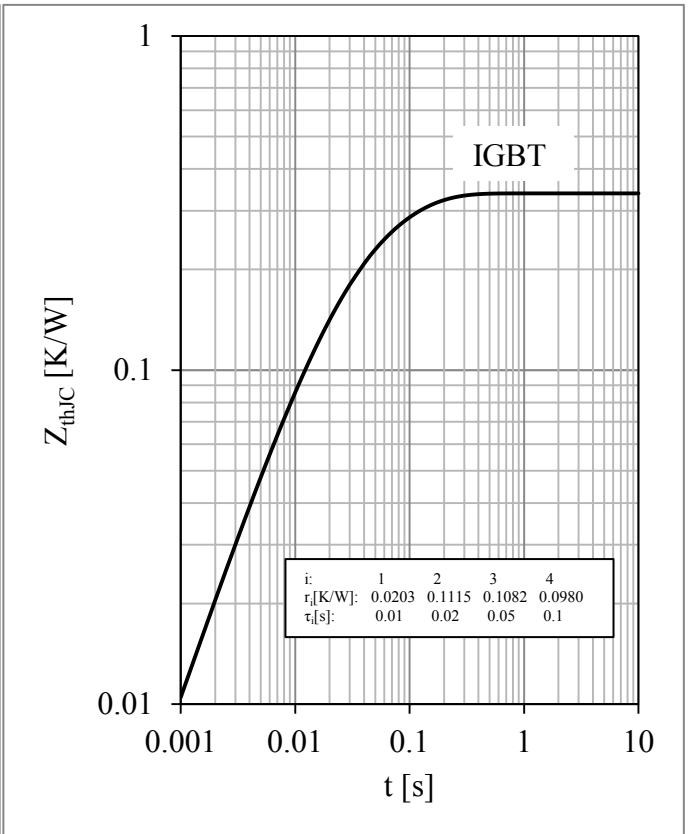


Fig 6. IGBT-inverter Transient Thermal Impedance

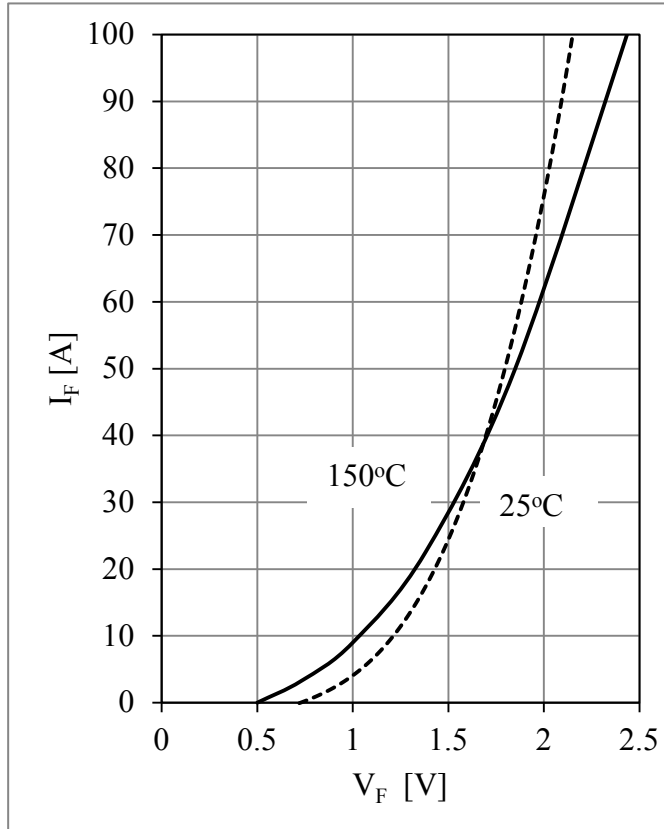
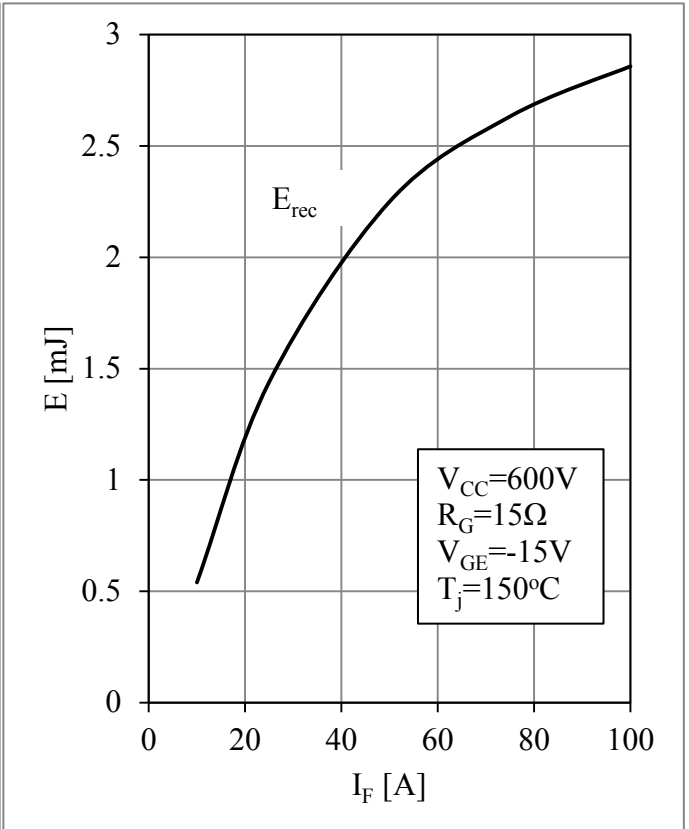


Fig 7. Diode-inverter Forward Characteristics

Fig 8. Diode-inverter Switching Loss vs. I_F

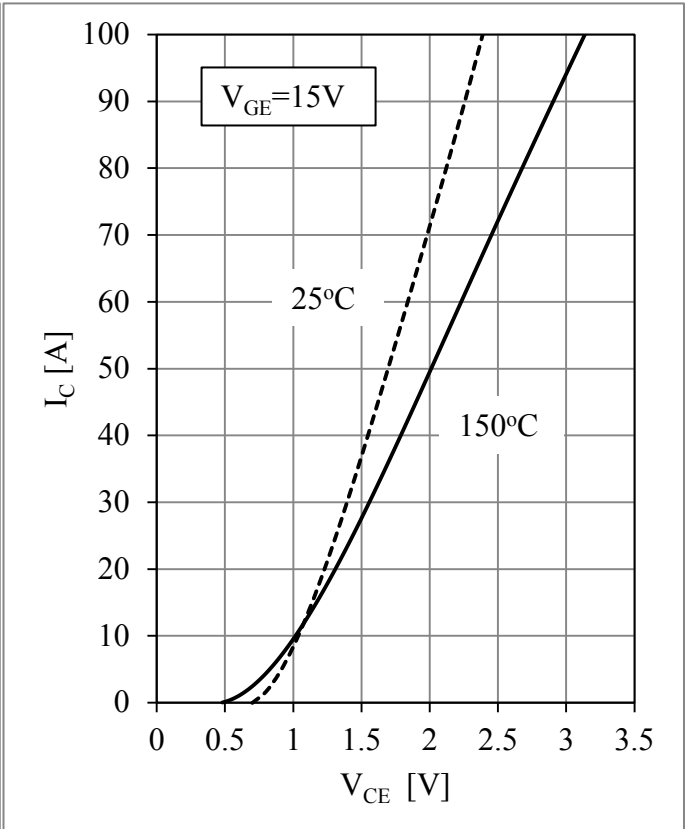
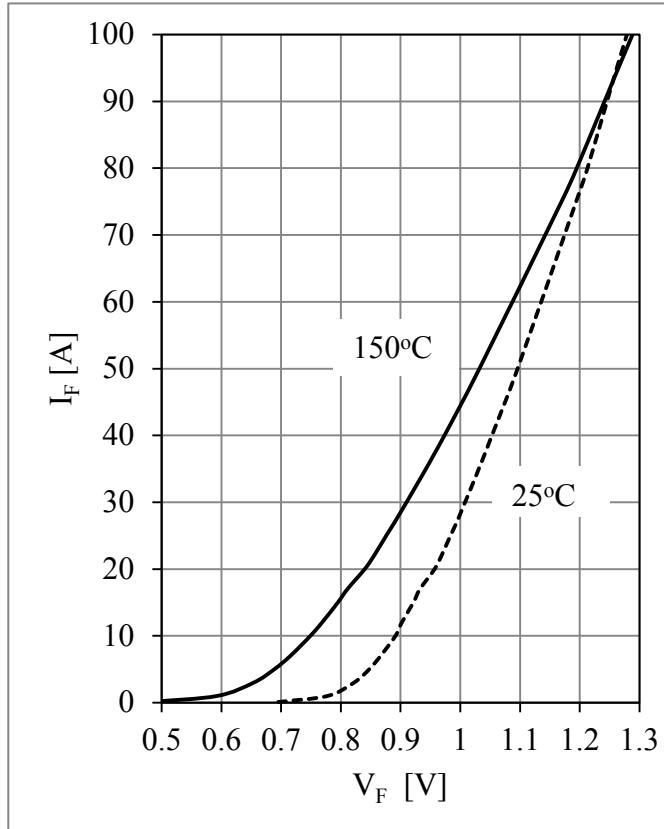
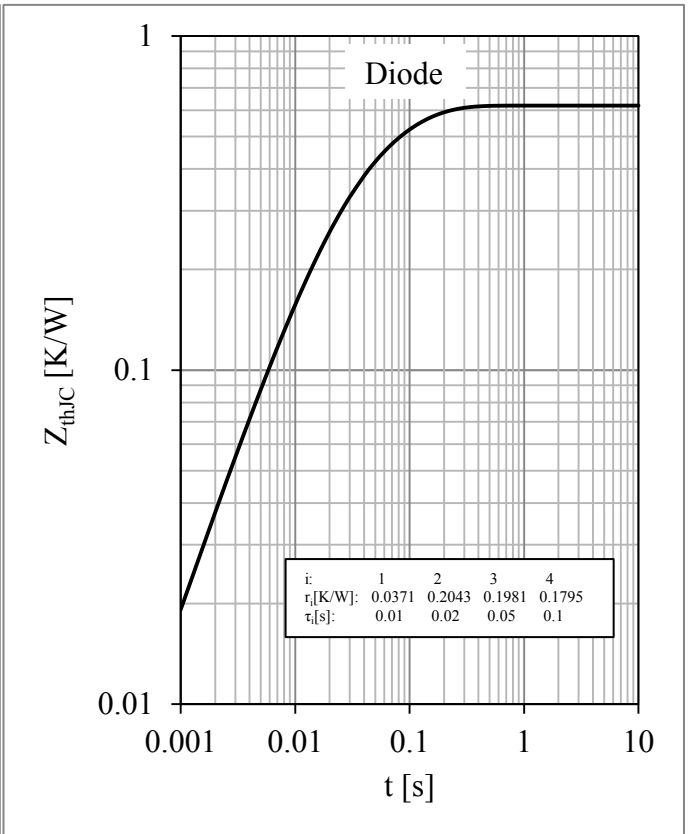
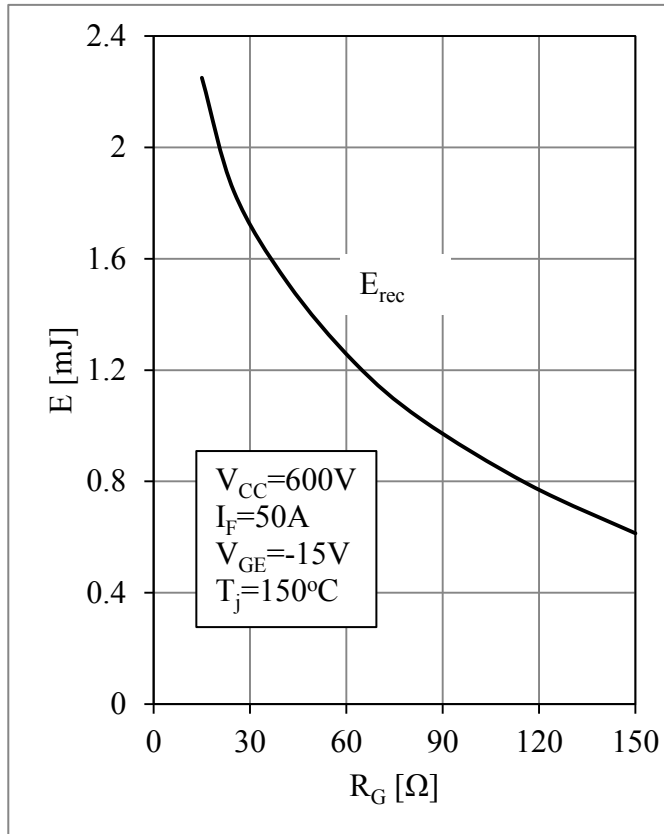


Fig 11. Diode-rectifier Forward Characteristics

Fig 12. IGBT-brake-chopper Output Characteristics

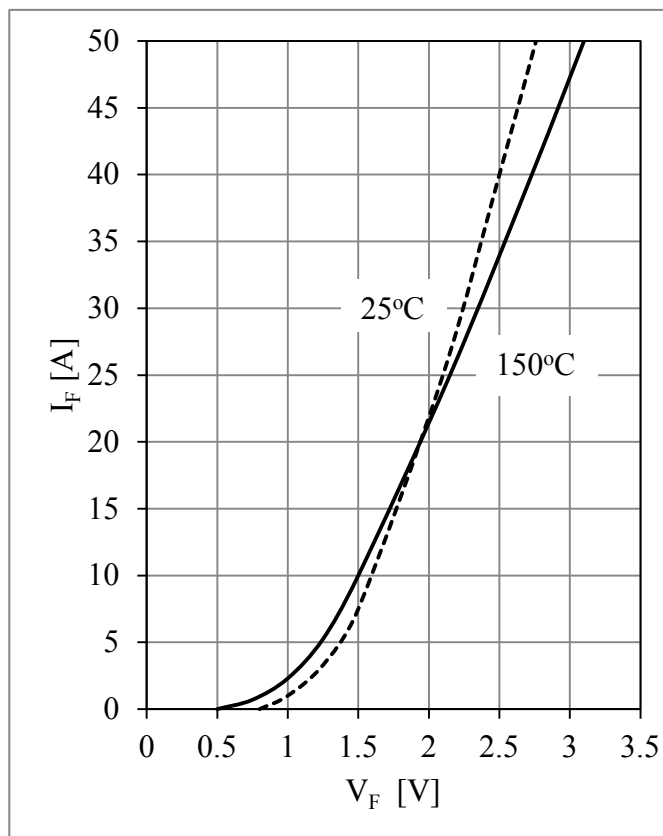


Fig 13. Diode-brake-chopper Forward Characteristics

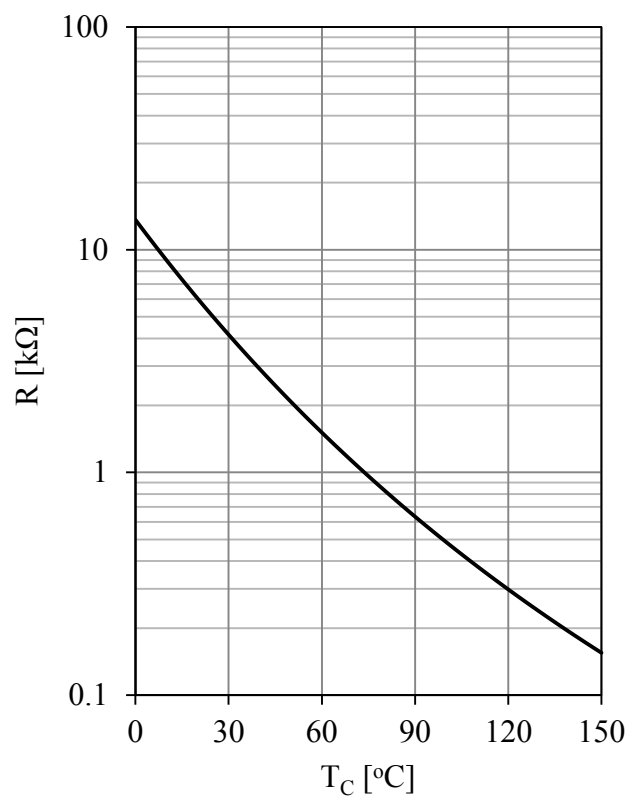
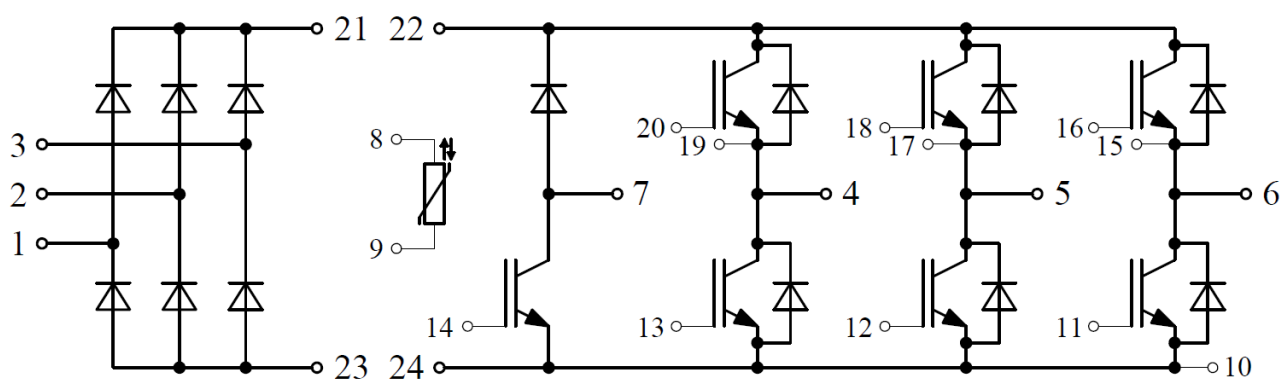


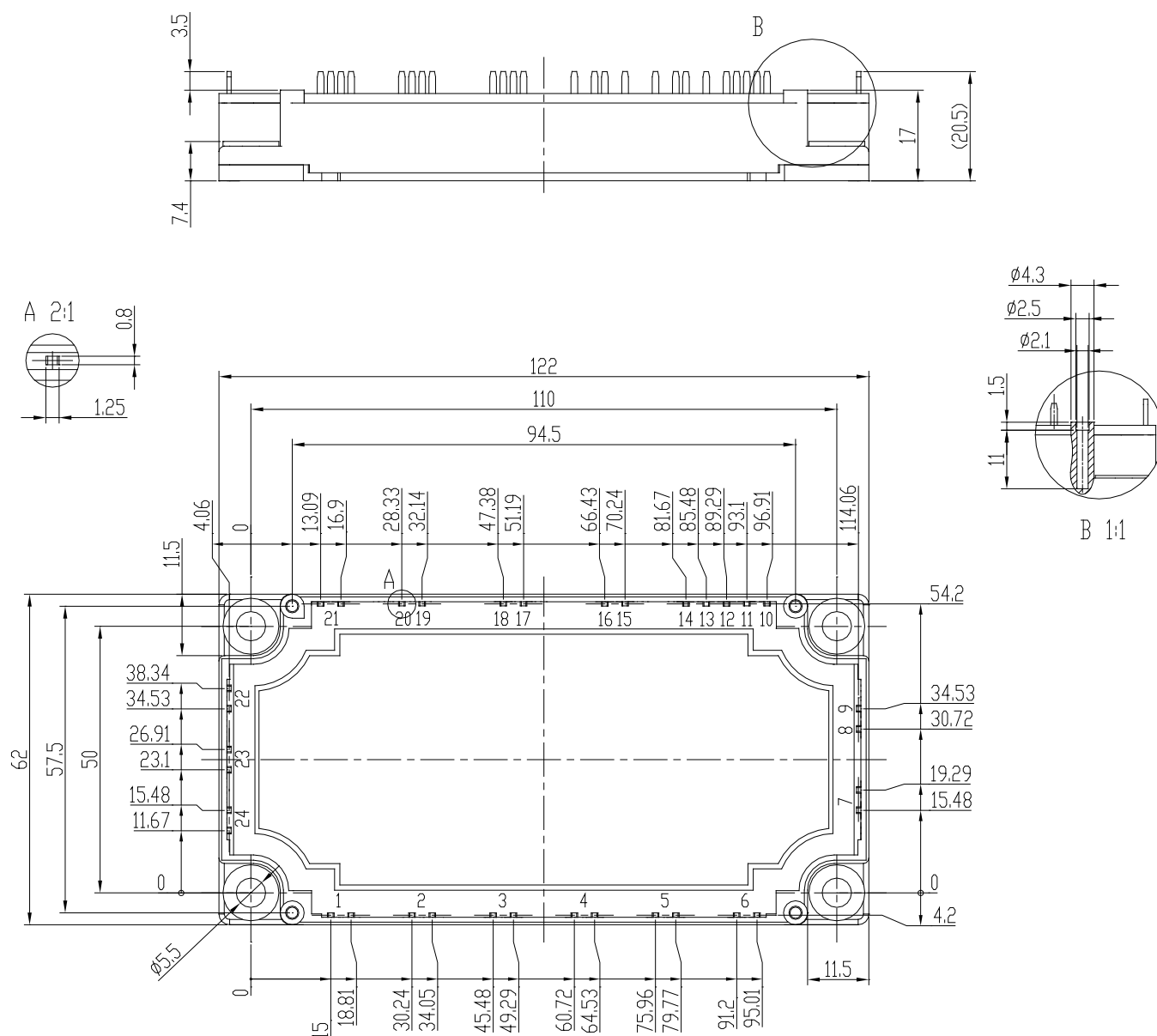
Fig 14. NTC Temperature Characteristic

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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